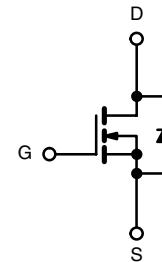
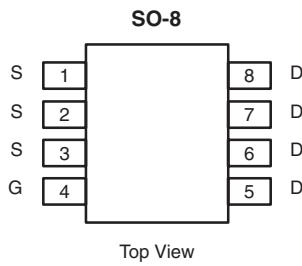


N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0055 at $V_{GS} = 10$ V	26	30 nC
	0.0068 at $V_{GS} = 4.5$ V	23	

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- 100 % R_g Tested



Ordering Information: Si4356ADY-T1-E3 (Lead (Pb)-free)
Si4356ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	30		
Gate-Source Voltage	V_{GS}	± 12	V	
Continuous Drain Current ($T_J = 150$ °C)	I_D	26		A
		21		
		17 ^{b, c}		
		14 ^{b, c}		
Pulsed Drain Current	I_{DM}	50		
Continuous Source-Drain Diode Current	I_S	55		
		2.7 ^{b, c}		
Single Pulse Avalanche Current	I_{AS}	40		
Avalanche Energy	E_{AS}	80	mJ	
Maximum Power Dissipation	P_D	6.5		W
		4.2		
		3 ^{b, c}		
		2 ^{b, c}		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	34	41	
Maximum Junction-to-Foot (Drain)	Steady State R_{thJF}	15	19	°C/W

Notes:

- Based on $T_C = 25$ °C.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under Steady State conditions is 80 °C/W.

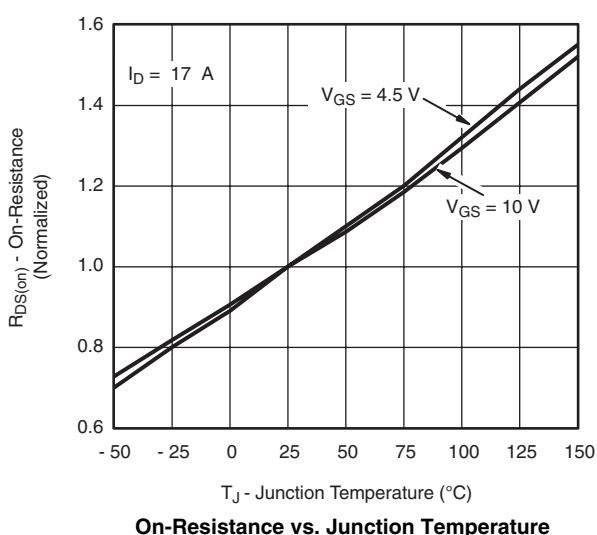
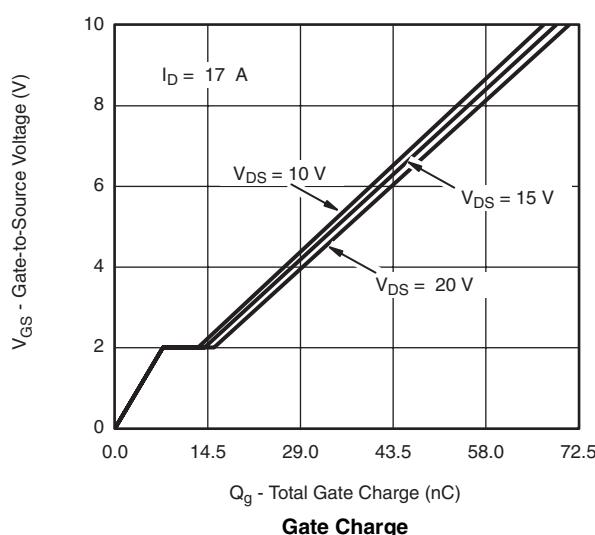
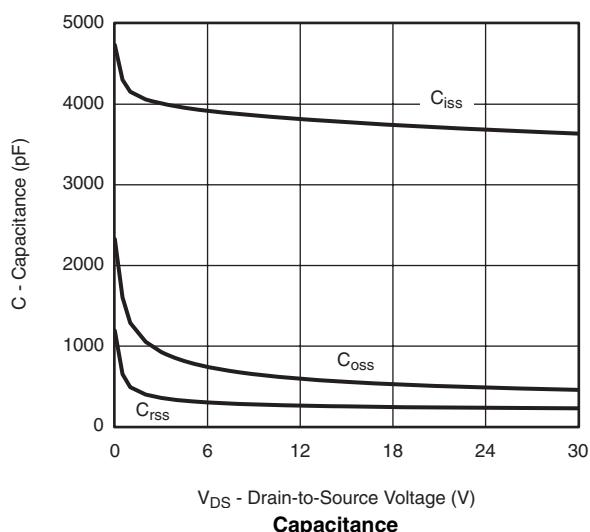
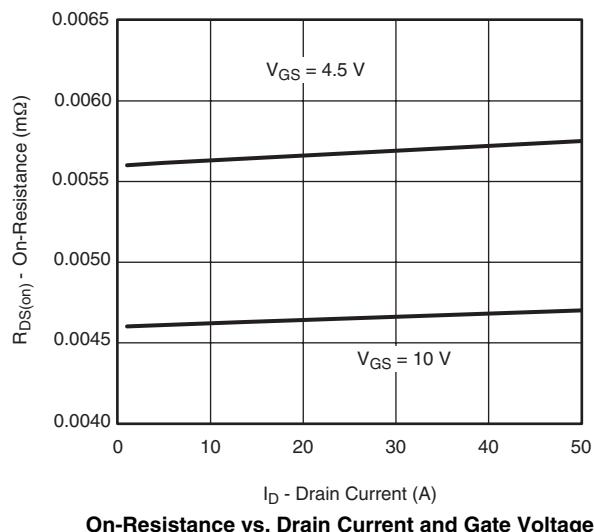
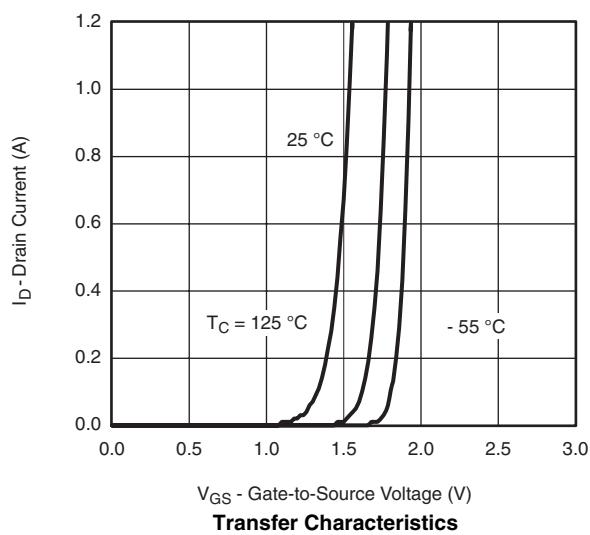
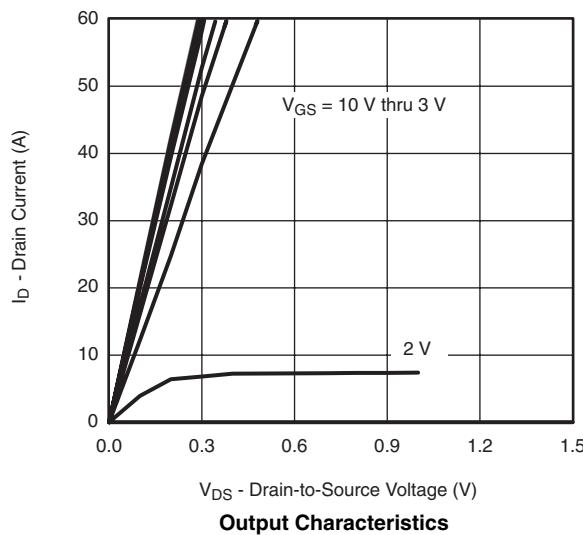
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 1 \text{ mA}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		30		$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			- 4.5		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	0.6		2	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$		0.0046	0.0055	Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 15 \text{ A}$		0.0056	0.0068	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 20 \text{ A}$		80		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		3780		pF
Output Capacitance	C_{oss}			555		
Reverse Transfer Capacitance	C_{rss}			250		
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 17 \text{ A}$		69	105	nC
		$V_{DS} = 15 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 17 \text{ A}$		30	45	
Gate-Source Charge	Q_{gs}			7.5		
Gate-Drain Charge	Q_{gd}			6.5		
Gate Resistance	R_g	$f = 1 \text{ MHz}$		1.25	1.9	Ω
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{DD} = 15 \text{ V}$, $R_L = 1.5 \Omega$ $I_D \geq 10 \text{ A}$, $V_{GEN} = 4.5 \text{ V}$, $R_g = 1 \Omega$		40	60	ns
Rise Time	t_r			95	145	
Turn-Off Delay Time	$t_{d(\text{off})}$			55	85	
Fall Time	t_f			9	15	
Turn-on Delay Time	$t_{d(\text{on})}$			12	20	
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(\text{off})}$			57	90	
Fall Time	t_f			9	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			5.5	A
Pulse Diode Forward Current ^a	I_{SM}				50	
Body Diode Voltage	V_{SD}	$I_S = 2.7 \text{ A}$		0.72	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 10 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		33	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}			27	40	
Reverse Recovery Fall Time	t_a			16		ns
Reverse Recovery Rise Time	t_b			17		

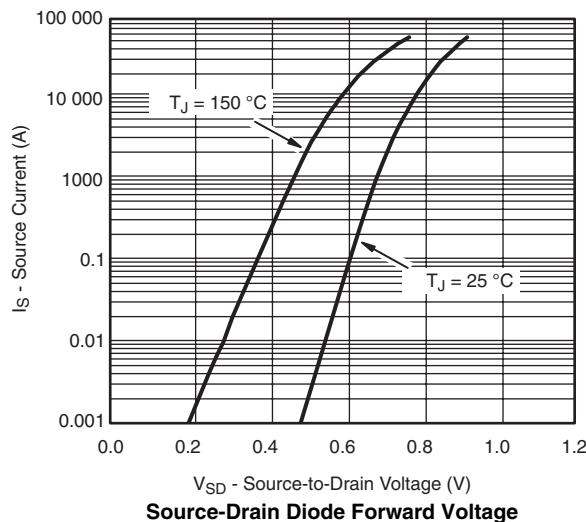
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing.

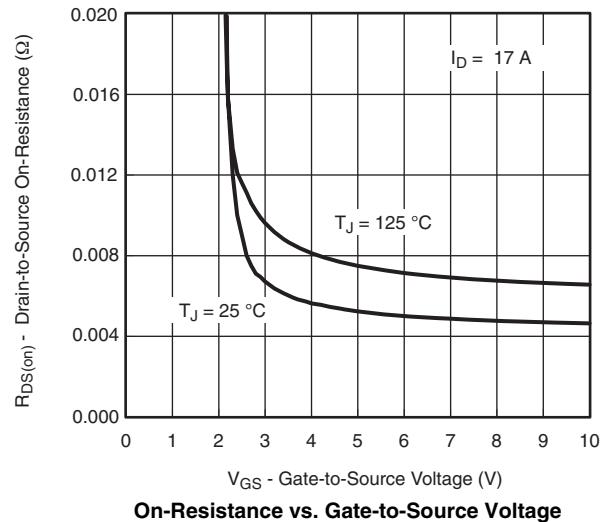
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


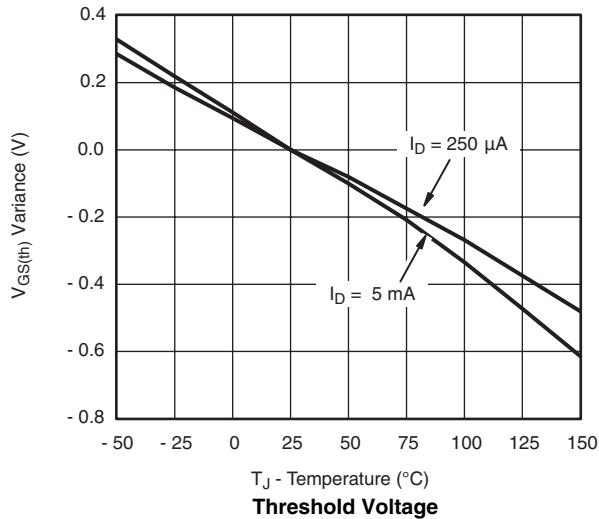
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



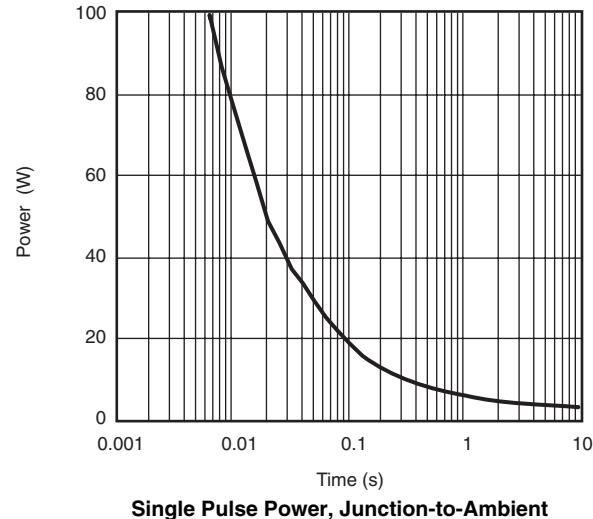
Source-Drain Diode Forward Voltage



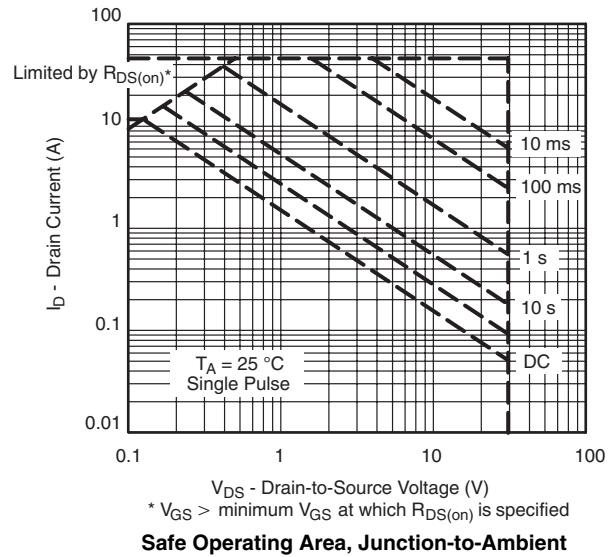
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

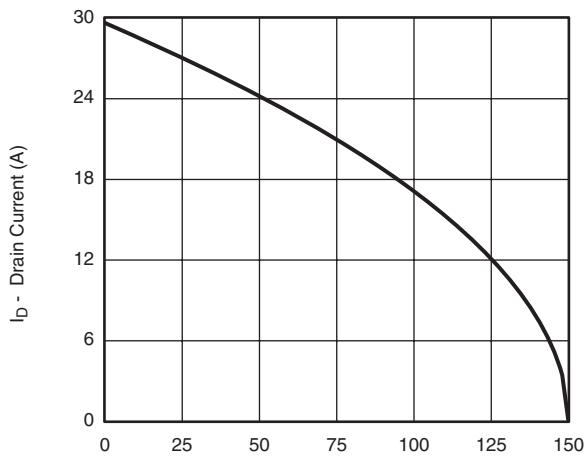


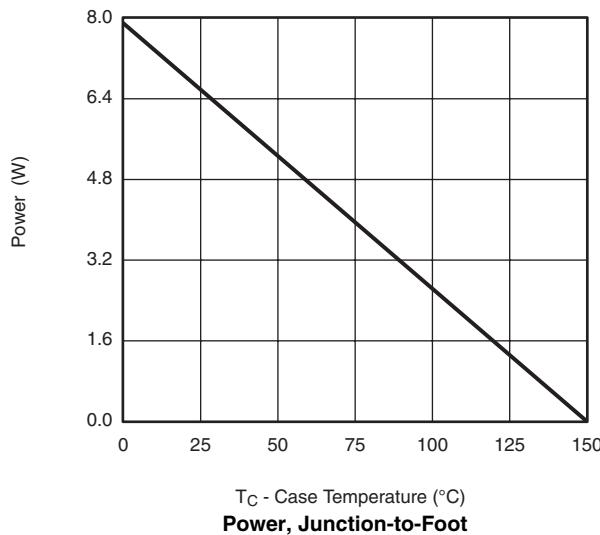
Single Pulse Power, Junction-to-Ambient

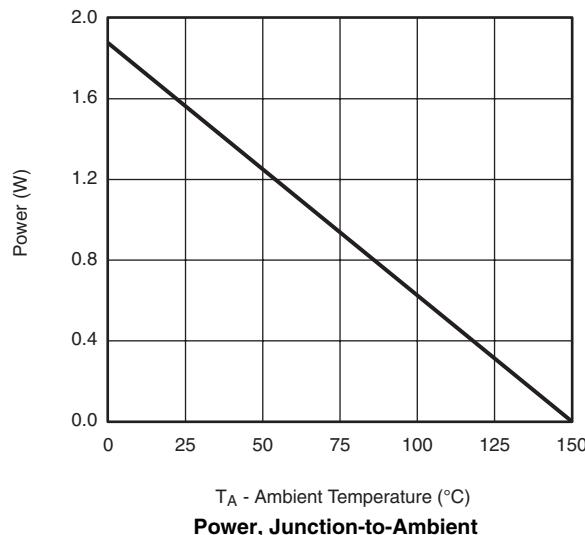


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

 T_C - Case Temperature (°C)

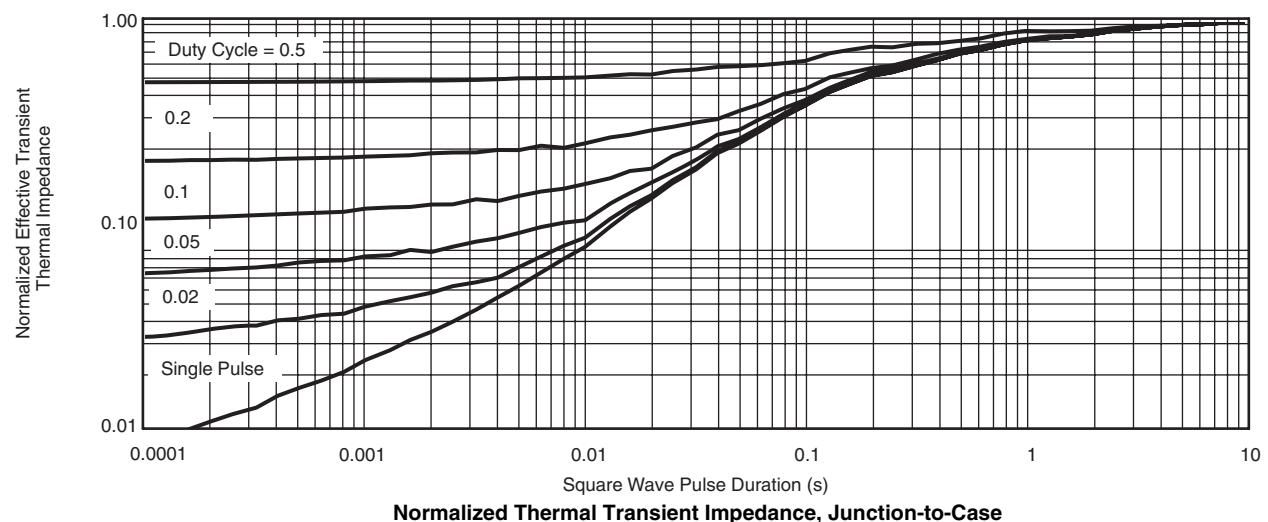
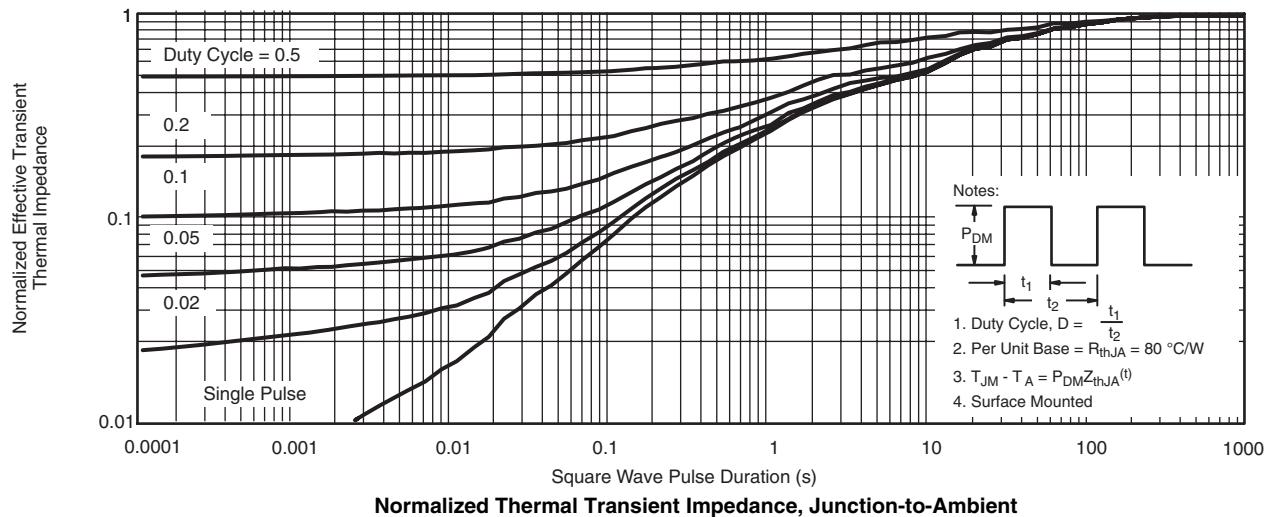
Current Derating*

 T_C - Case Temperature (°C)

Power, Junction-to-Foot

 T_A - Ambient Temperature (°C)

Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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